IN THE TITLE

~~SUBSTRATE~~ METHOD OF MANUFACTURING A SUBSTRATE HAVING SHALLOW TRENCH ISOLATION ~~AND METHOD OF MANUFACTURING THE SAME~~

IN THE SPECIFICATION

Please replace the paragraph beginning at page 19, line 22, with the following rewritten paragraph:

(b) Then, as shown in FIG. 3B, an oxide film 7 is deposited using organic silicon source such as TEOS ($Si(OC_2H_5)_4$) after the substrate is rinsed. Prior to deposition of the oxide film 7, a thin thermal oxidation film 7', illustrated in one groove 6 of Fig 3A with a dashed line, or Si_3N_4 film may be grown. In order to perfectly bury the grooves 6, the oxide film 7 is formed on the entirety of the Si substrate to have a 1.1 μm thickness, for example, which is thicker than the depth of the grooves 6. As material buried in the grooves 6, organic silicon source to which oxidizing agent such as N_2O, O_2, or O_3 is added may also be employed. In addition, the grooves 6 may be buried by the silicon oxide film in terms of CVD using, as source material, organic silicon source, silicon-hydrogen compound such as SiH_4, or silicon chloride such as $SiCl_4$ alone. Otherwise mixed material composed of two kinds of the above materials may be also used as CVD source material. Also oxide may be added to respective CVD materials.